



Thermal Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
P_D	Power Dissipation	290	mW
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	430	$^\circ\text{C}/\text{W}$

Electrical Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
V_R	Breakdown Voltage	$I_R = 100 \mu\text{A}$	30		V
		$I_F = 2.0 \text{ mA}$	260	330	mV
V_F	Forward Voltage	$I_F = 15 \text{ mA}$		450	mV
		$I_F = 100 \text{ mA}$		0.8	V

Typical Performance Characteristics

Figure 1. Forward Voltage vs. Temperature

Figure 2. Reverse Leakage Current vs. Temperature

Figure 3. Capacitance vs. Reverse Bias Voltage

Physical Dimensions

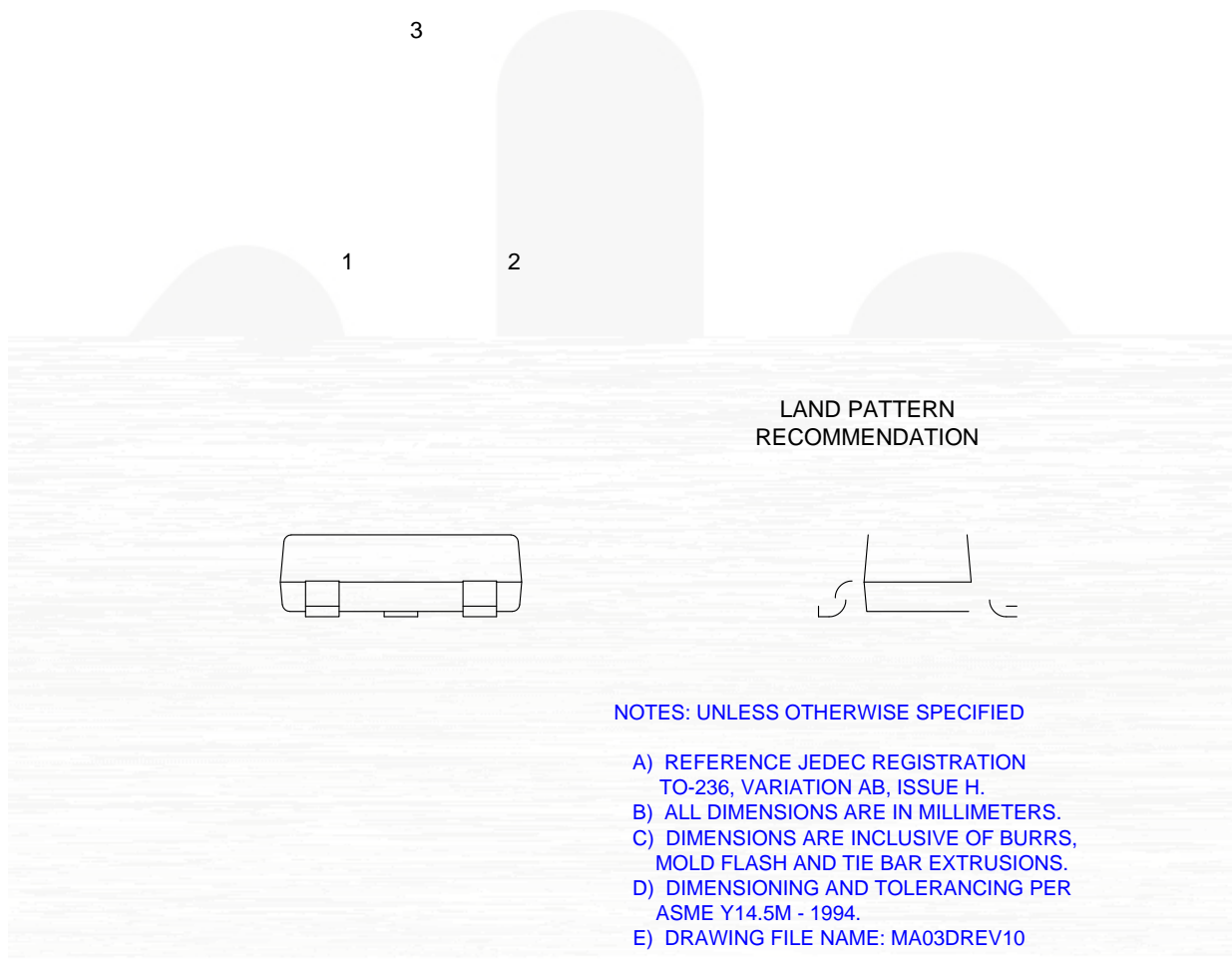


Figure 4. 3-LEAD, SOT23, JEDEC TO-236, LOW PROFILE

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